

WHAT IS CLAIMED IS:

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1. A semiconductor device, comprising:
 - a gate electrode;
 - an insulating layer on the gate electrode;
 - 10 a first electrode on the insulating layer;
 - a second electrode on the insulating layer at an interval with the first electrode;
 - an organic semiconductor layer disposed in the interval between the first electrode and the second
 - 15 electrode and covering at least part of the first electrode and the second electrode; and
 - a first resistance layer formed on the organic semiconductor layer and having an electrical resistance lower than an electrical resistance of the
 - 20 organic semiconductor layer.
- 25 2. The semiconductor device as claimed in

claim 1, wherein both a distance from the first electrode to the first resistance layer and a distance from the second electrode to the first resistance layer are shorter than the interval between the first 5 electrode and the second electrode.

10 3. The semiconductor device as claimed in claim 1, wherein one of the first electrode and the second electrode is in contact with the first resistance layer.

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4. The semiconductor device as claimed in claim 1, further comprising a second resistance layer 20 formed at least at one of the position between the first resistance layer and the organic semiconductor layer, the position between the first electrode and the organic semiconductor layer, and the position between the second electrode and the organic semiconductor 25 layer,

wherein the second resistance layer has an electrical resistance so that carriers in the organic semiconductor layer are allowed to tunnel through the second resistance layer when a voltage of a 5 predetermined value or more than the predetermined value is applied across the second resistance layer.

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5. The semiconductor device as claimed in claim 1, wherein

at least one of the first electrode, the second electrode and the first resistance layer is in 15 contact with the organic semiconductor layer; and an interface between one of the first electrode, the second electrode and the first resistance layer rectifies an electrical current therethrough.

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6. The semiconductor device as claimed in 25 claim 1, wherein the first resistance layer is formed

to be one of a plate shape, an inter-digital shape, a grating shape, and a disk shape.

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7. The semiconductor device as claimed in claim 1, wherein a substrate is beneath the gate electrode.

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8. A semiconductor device, comprising:

15 a first electrode;
a second electrode at an interval with the first electrode;
an organic semiconductor layer disposed in the interval between the first electrode and the second electrode and covering at least part of the first electrode and the second electrode;

20 a first resistance layer formed on the organic semiconductor layer and having an electrical resistance lower than an electrical resistance of the 25 organic semiconductor layer;

an insulating layer on the first resistance layer; and

a gate electrode on the insulating layer.

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9. The semiconductor device as claimed in
claim 8, further comprising a second resistance layer
10 formed at least at one of the position between the
first resistance layer and the organic semiconductor
layer, the position between the first electrode and the
organic semiconductor layer, and the position between
the second electrode and the organic semiconductor
15 layer,

wherein the second resistance layer has an
electrical resistance so that carriers in the organic
semiconductor layer are allowed to tunnel through the
second resistance layer when a voltage of a
20 predetermined value or more than the predetermined
value is applied across the second resistance layer.

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10. The semiconductor device as claimed in
claim 8, wherein a substrate is beneath the first
electrode, the second electrode and the organic
semiconductor layer.

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11. A semiconductor device, comprising:

10 an organic semiconductor layer;
a first resistance layer beneath the organic
semiconductor layer and having an electrical resistance
lower than an electrical resistance of the organic
semiconductor layer;

15 a first electrode on the organic
semiconductor layer;

a second electrode on the organic
semiconductor layer at an interval with the first
electrode;

20 an insulating layer disposed in the interval
between the first electrode and the second electrode
and covering the first electrode and the second
electrode; and

a gate electrode on the insulating layer,
25 wherein the first resistance layer has an

electrical resistance lower than that of the organic semiconductor layer.

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12. The semiconductor device as claimed in
claim 11, further comprising a second resistance layer
formed at least at one of the position between the
10 first resistance layer and the organic semiconductor
layer, the position between the first electrode and the
organic semiconductor layer, and the position between
the second electrode and the organic semiconductor
layer,

15 wherein the second resistance layer has an
electrical resistance so that carriers in the organic
semiconductor layer are allowed to tunnel through the
second resistance layer when a voltage of a
predetermined value or more than the predetermined
20 value is applied across the second resistance layer.

25 13. The semiconductor device as claimed in

claim 11, wherein a substrate is beneath the first resistance layer.

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14. A semiconductor device, comprising:
 - a gate electrode;
 - an insulating layer on the gate electrode;
 - 10 a first resistance layer on the insulating layer;
 - an organic semiconductor layer on the first resistance layer;
 - a first electrode on the organic semiconductor layer; and
 - 15 a second electrode on the organic semiconductor layer at an interval with the first electrode,
 - wherein the first resistance layer has an electrical resistance lower than an electrical resistance of the organic semiconductor layer.

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15. The semiconductor device as claimed in
claim 14, wherein two opposite ends of the first
resistance layer are covered by the organic
semiconductor layer.

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16. The semiconductor device as claimed in
10 claim 14, further comprising a second resistance layer
formed at least at one of the position between the
first resistance layer and the organic semiconductor
layer, the position between the first electrode and the
organic semiconductor layer, and the position between
15 the second electrode and the organic semiconductor
layer,

wherein the second resistance layer has an
electrical resistance so that carriers in the organic
semiconductor layer are allowed to tunnel through the
20 second resistance layer when a voltage of a
predetermined value or more than the predetermined
value is applied across the second resistance layer.

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17. The semiconductor device as claimed in
claim 14, wherein a substrate is beneath the gate
electrode.

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18. The semiconductor device as claimed in
10 claim 1, wherein the organic semiconductor layer is
formed from

at least one organic material selected from
the group consisting of poly(N-vinylcarbazole)
derivatives, poly(γ -(carbazolylethyl)glutamate)
15 derivatives, poly(vinylphenanthrene) derivatives,
polysilane derivatives, oxazole derivatives, oxadiazole
derivatives, imidazole derivatives, arylamine
derivatives such as monoarylamine derivatives and
triarylamine derivatives, benzidine derivatives,
20 diarylmethane derivatives, triarylmethane derivatives,
styrylanthracene derivatives, pyrazoline derivatives,
divinylbenzene derivatives, hydrazone derivatives,
indene derivatives, indenone derivatives, butadiene
derivatives, pyrene derivatives such as pyrene-
25 formaldehyde and poly(vinylpyrene), stilbene

derivatives such as α -phenylstilbene derivatives, and
bis-stilbene derivatives, enamine derivatives,
fluorenone and derivatives thereof, poly(fluorenone)
and derivatives thereof, and thiophene derivatives such
5 as poly(alkylthiophene), or

at least one organic material selected from
the group consisting of pentacene, tetracene, bis-azo
pigments, tris-azo pigments, poly-azo pigments,
triarylmethane-based pigments, thiazine-based pigments,
10 oxazine-based pigments, xanthene-based pigments,
cyanine pigments, styryl pigments, pyrylium-based
pigments, quinacridone-based pigments, indigo-based
pigments, perylene-based pigments, polycyclic quinone-
based pigments, bis(benzimidazole)-based pigments,
15 indanthrone-based pigments, squarylium-based pigments,
anthraquinone-based pigments, and phthalocyanine-based
pigments such as copper phthalocyanine and
titanylphthalocyanine.

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19. The semiconductor device as claimed in
claim 1, wherein the first resistance layer is formed
25 from at least one electrically conductive material of

polyacetylene-based electrically conductive polymers,
polyphenylene-based electrically conductive polymers
such as poly(para-phenylene) and derivatives thereof
and poly(phenylene vinylene) and derivatives thereof,
5 heterocyclic electrically conductive polymers such as
polypyrrole and derivatives thereof, polythiophene and
derivatives thereof, poly(ethylenedioxathiophene) and
derivatives thereof, and polyfuran and derivatives
thereof, ionic electrically conductive polymers such as
10 polyaniline and derivatives thereof, and metals of
chromium (Cr), tantalum (Ta), titanium (Ti), copper
(Cu), aluminum (Al), molybdenum (Mo), tungsten (W),
nickel (Ni), gold (Au), palladium (Pd), platinum (Pt),
silver (Ag), and tin (Sn).

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20. The semiconductor device as claimed in
20 claim 1, wherein the first resistance layer comprises
at least one dopant with a low vapor pressure including
one or more of poly(sulfonic acid),
poly(styrenesulfonic acid), naphthalenesulfonic acid,
and alkynaphthalenesulfonic acid.

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21. The semiconductor device as claimed in
5 claim 1, wherein each of the first electrode, the
second electrode, and the gate electrode is formed from
at least one of chromium (Cr), tantalum (Ta),
titanium (Ti), copper (Cu), aluminum (Al), molybdenum
(Mo), tungsten (W), nickel (Ni), gold (Au), palladium
10 (Pd), platinum (Pt), silver (Ag), and tin (Sn), or
at least one electrically conductive polymer
of polyacetylene-based electrically conductive polymers,
polyphenylene-based electrically conductive polymers
such as poly(para-phenylene) and derivatives thereof
15 and poly(phenylene vinylene) and derivatives thereof,
heterocyclic electrically conductive polymers such as
polypyrrole and derivatives thereof, polythiophene and
derivatives thereof, poly(ethylenedioxythiophene) and
derivatives thereof, and polyfuran and derivatives
20 thereof, and ionic electrically conductive polymers
such as polyaniline and derivatives thereof.

22. The semiconductor device as claimed in
claim 1, wherein the insulating layer is formed from
at least one resin selected from the group
consisting of thermoplastic resins such as styrene-
5 based polymers such as copoly(styrene/butadiene),
copoly(styrene/acrylonitrile),
terpoly(styrene/acrylonitrile/butadiene),
copoly(styrene/maleic acid), and copoly(styrene/acrylic
acid), polyethylene-based resins such as
10 copoly(ethylene/vinyl acetate), and chlorinated
polyethylenes, polypropylene, vinyl chloride-based
resins such as copoly(vinyl chloride/vinyl acetate),
polyester alkyd resins, polyamides, polyurethanes,
polycarbonates, polyallylates, polysulfones, diallyl
15 phthalate resin, poly(vinylbutyral) resin, polyether
resins, polyester resins, acrylic resin, silicone resin,
epoxy resins, phenolic resin, urea resin, melamine
resin, fluorocarbon resins such as PFA, PTFE, and PVDF,
Parylene resin, polyimide resins, and photo-setting
20 resins such as epoxyacrylates and urethane acrylates,
or
a metal oxide produced via oxidation of a
surface of an electrode layer formed from the metal.

23. The semiconductor device as claimed in
claim 1, wherein the insulating layer is formed from at
5 least a metal oxide film produced by coating and baking
a solution obtained via hydrolysis of a metal alkoxide
represented by one of the general formulas $M(OR)_n$ and
 $MR(OR')_{n-1}$, wherein each of R and R' is an organic group
such as an alkyl group and a phenyl group, M is a metal
10 in one of IVA through VIIA groups, VIII group, and IB
through VIB groups of the periodic table, and n is an
ionic valence of the metal M.

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24. The semiconductor device as claimed in
claim 4, wherein the second resistance layer is formed
from at least one resin selected from the group
20 consisting of thermoplastic resins such as styrene-
based polymers such as copoly(styrene/butadiene),
copolystyrene/acrylonitrile),
terpoly(styrene/acrylonitrile/butadiene),
copolystyrene/maleic acid), and copoly(styrene/acrylic
25 acid), polyethylene-based resins such as

copoly(ethylene/vinyl acetate), and chlorinated polyethylenes, polypropylene, vinyl chloride-based resins such as copoly(vinyl chloride/vinyl acetate), polyester alkyd resins, polyamides, polyurethanes, 5 polycarbonates, polyallylates, polysulfones, diallyl phthalate resin, poly(vinylbutyral) resin, polyether resins, polyester resins, acrylic resin, silicone resin, epoxy resins, phenolic resin, urea resin, melamine resin, fluorocarbon resins such as PFA, PTFE, and PVDF, 10 Parylene resin, polyimide resins, and photo-setting resins such as epoxyacrylates and urethane acrylates, or

a metal oxide produced via oxidation of a surface of at least one of the first electrode and the 15 second electrode.

20 25. The semiconductor device as claimed in claim 4, wherein the second resistance layer is formed from at least a metal oxide film produced by coating and baking a solution obtained via hydrolysis of a metal alkoxide represented by one of the general formulas $M(OR)_n$ and $MR(OR')_{n-1}$, wherein each of R and R'

is an organic group such as an alkyl group and a phenyl group, M is a metal in one of IVA through VIIA groups, VIII group, and IB through VIB groups of the periodic table, and n is an ionic valence of the metal M.

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26. The semiconductor device as claimed in
10 claim 1, further comprising:

a first power supply conducting a current
between the first electrode and the second electrode;
and

a second power supply applying a voltage to
15 the gate electrode.

20 27. An electroluminescent display device,
comprising a plurality of semiconductor devices, each
semiconductor device including:

a gate electrode;
an insulating layer on the gate electrode;
25 a first electrode on the insulating layer;

a second electrode on the insulating layer
at an interval with the first electrode;
an organic semiconductor layer disposed in
the interval between the first electrode and the second
5 electrode and covering at least part of the first
electrode and the second electrode; and
a first resistance layer formed on the
organic semiconductor layer and having an electrical
resistance lower than an electrical resistance of the
10 organic semiconductor layer.

15 28. An electroluminescent display device
including a plurality of semiconductor devices and a
plurality of light emitting elements arranged in a
matrix manner on a substrate,

each of the semiconductor devices
20 comprising:
a gate electrode on the substrate;
an insulating layer covering ends and a
surface of the gate electrode;
a first electrode on the insulating layer;
25 a second electrode on the insulating layer

at an interval with the first electrode;

an organic semiconductor layer disposed in the interval between the first electrode and the second electrode and covering at least part of the first 5 electrode and the second electrode; and

a first resistance layer formed on the organic semiconductor layer and having an electrical resistance lower than an electrical resistance of the organic semiconductor layer,

10 the light emitting element comprising:

a transparent electrode on the substrate;

an electroluminescent layer on the transparent electrode; and

a cathode on the electroluminescent layer,

15 wherein the first electrode is electrically connected with the transparent electrode.

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29. A liquid crystal display device, comprising a semiconductor device including:

a gate electrode;

an insulating layer on the gate electrode;

25 a first electrode on the insulating layer;

a second electrode on the insulating layer
at an interval with the first electrode;

an organic semiconductor layer disposed in
the interval between the first electrode and the second
5 electrode and covering at least part of the first
electrode and the second electrode; and

a first resistance layer formed on the
organic semiconductor layer and having an electrical
resistance lower than an electrical resistance of the
10 organic semiconductor layer.

15 30. A calculating device, comprising at
least one of a NOT circuit, a NAND circuit, and a NOR
circuit each including a plurality of semiconductor
devices,

each of the semiconductor devices including:
20 a gate electrode;
an insulating layer on the gate electrode;
a first electrode on the insulating layer;
a second electrode on the insulating layer
at an interval with the first electrode;

25 an organic semiconductor layer disposed in

the interval between the first electrode and the second electrode and covering at least part of the first electrode and the second electrode; and

5 a first resistance layer formed on the organic semiconductor layer and having an electrical resistance lower than an electrical resistance of the organic semiconductor layer.

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31. The semiconductor device as claimed in claim 1, wherein the organic semiconductor layer includes a dielectric material.

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32. The semiconductor device as claimed in 20 claim 31, wherein the dielectric material is selected from

styrene-based polymers such as copoly(styrene/butadiene), copoly(styrene/acrylonitrile), 25 terpoly(styrene/acrylonitrile/butadiene),

copoly(styrene/maleic acid), and copoly(styrene/acrylic acid), polyethylene-based resins such as copoly(ethylene/vinyl acetate), and chlorinated polyethylenes, polypropylene, vinyl chloride-based 5 resins such as copoly(vinyl chloride/vinyl acetate), polyester alkyd resins, polyamides, polyurethanes, polycarbonates, polyallylates, polysulfones, diallyl phthalate resin, poly(vinylbutyral) resin, polyether resins, polyester resins, acrylic resin, silicone resin, 10 epoxy resins, phenolic resin, urea resin, melamine resin, fluorocarbon resins such as PFA, PTFE, and PVDF, Parylene resin, polyimide resins, and photo-setting resins such as epoxyacrylates and urethane acrylates,

a metal oxide film produced by baking a

15 solution obtained via hydrolysis of a metal alkoxide represented by one of the general formulas $M(OR)_n$ and $MR(OR')_{n-1}$, in which each of R and R' is an organic group such as an alkyl group and a phenyl group, M is a metal in one of IVA through VIIA groups, VIII group, 20 and IB through VIB groups of the periodic table, and n is an ionic valence of the metal M,

an oxide of one of Al, Ta, and W, Si, and a nitride of Si.